

MOS FIELD EFFECT TRANSISTOR μ PA2711GR

SWITCHING P-CHANNEL POWER MOS FET

DESCRIPTION

The μ PA2711GR is P-Channel MOS Field Effect Transistor designed for power management applications of notebook computers and Li-ion battery protection circuit.

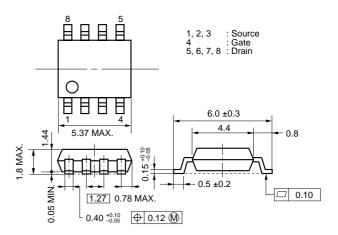
FEATURES

- · Low on-state resistance
 - $R_{DS(on)1} = 9 \text{ m}\Omega \text{ MAX.} (V_{GS} = -10 \text{ V}, I_D = -6.5 \text{ A})$
 - $R_{DS(on)2} = 15 \text{ m}\Omega \text{ MAX}. \text{ (V}_{GS} = -4.5 \text{ V}, I_{D} = -6.5 \text{ A})$
 - $R_{DS(on)3}$ = 20 $m\Omega$ MAX. (Vgs = -4.0 V, Ip = -6.5 A)
- Low Ciss: Ciss = 2450 pF TYP.
- Small and surface mount package (Power SOP8)

ORDERING INFORMATION

PART NUMBER	PACKAGE
μPA2711GR	Power SOP8

PACKAGE DRAWING (Unit: mm)



ABSOLUTE MAXIMUM RATINGS (TA = 25°C, Unless otherwise noted, All terminals are connected.)

Drain to Source Voltage (Vgs = 0 V)	VDSS	-30	V	
Gate to Source Voltage (VDS = 0 V)	Vgss	∓20	V	EQUIVALENT CIRCUIT
Drain Current (DC)	I _{D(DC)}	∓13	Α	-
Drain Current (pulse) Note1	I _{D(pulse)}	∓52	Α	Drain
Total Power Dissipation Note2	P _{T1}	2	W	•
Total Power Dissipation Note3	P _{T2}	2	W	₩ Body
Channel Temperature	Tch	150	°C	Gate
Storage Temperature	Tstg	-55 to + 150	°C	
Single Avalanche Current Note4	las	-13	Α	
Single Avalanche Energy Note4	Eas	16.9	mJ	Source

Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

- 2. Mounted on ceramic substrate of 1200 mm² x 2.2 mm
- 3. Mounted on a glass epoxy board (1 inch x 1 inch x 0.8 mm), PW = 10 sec
- **4.** Starting T_{ch} = 25°C, V_{DD} = -15 V, R_G = 25 Ω , L = 100 μ H, V_{GS} = -20 \rightarrow 0 V

Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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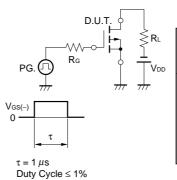
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CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = -30 V, V _{GS} = 0 V			-1	μА
Gate Leakage Current	Igss	V _{GS} = ∓20 V, V _{DS} = 0 V			∓100	μΑ
Gate Cut-off Voltage	V _{GS(off)}	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$	-1.0		-2.5	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = -10 V, I _D = -6.5 A	10	22		S
Drain to Source On-state Resistance Note	RDS(on)1	V _{GS} = -10 V, I _D = -6.5 A		7.4	9	mΩ
	RDS(on)2	$V_{GS} = -4.5 \text{ V}, I_{D} = -6.5 \text{ A}$		10	15	mΩ
	RDS(on)3	$V_{GS} = -4.0 \text{ V}, I_{D} = -6.5 \text{ A}$		12	20	mΩ
Input Capacitance	Ciss	V _{DS} = -10 V		2450		pF
Output Capacitance	Coss	V _{GS} = 0 V		740		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		410		pF
Turn-on Delay Time	t d(on)	$V_{DD} = -15 \text{ V}, I_D = -6.5 \text{ A}$		10		ns
Rise Time	tr	V _{GS} = -10 V		15		ns
Turn-off Delay Time	t d(off)	R _G = 10 Ω		230		ns
Fall Time	tf			130		ns
Total Gate Charge	Q _G	V _{DD} = -24 V		57		nC
Gate to Source Charge	Qss	V _G s = -10 V		6.3		nC
Gate to Drain Charge	Q _{GD}	I _D = −13 A		19		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = 13 A, V _{GS} = 0 V		0.81		V
Reverse Recovery Time	trr	I _F = 13 A, V _{GS} = 0 V		62		ns
Reverse Recovery Charge	Qrr	di/dt = 50 A/μs		31		nC

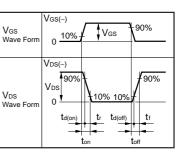
Note Pulsed

TEST CIRCUIT 1 AVALANCHE CAPABILITY

$PG. \bigcirc PG. \bigcirc PG.$

TEST CIRCUIT 2 SWITCHING TIME



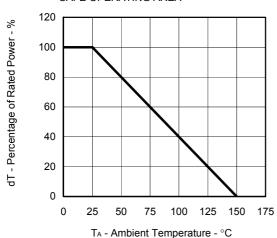


TEST CIRCUIT 3 GATE CHARGE

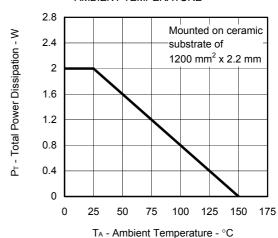
$$\begin{array}{c|c} D.U.T. \\ \hline \\ IG = -2 \text{ mA} \\ \hline \\ PG. \\ \hline \\ \end{array}$$

ELECTRICAL CHARACTERISTICS (TA = 25°C)

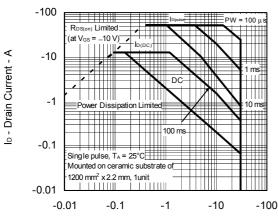
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE

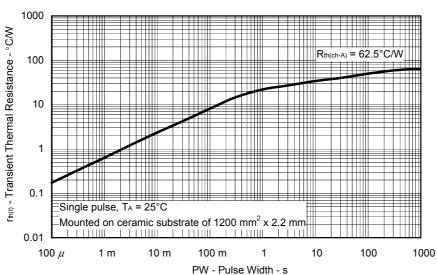


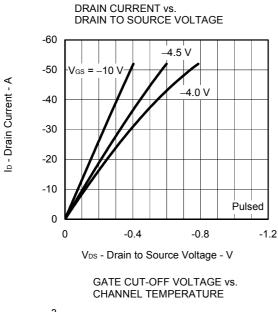
FORWARD BIAS SAFE OPERATING AREA

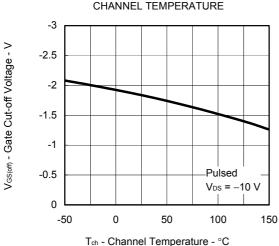


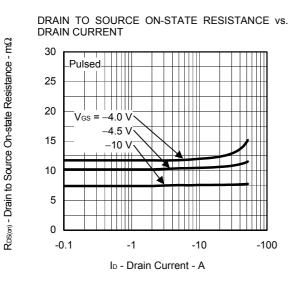
V_{DS} - Drain to Source Voltage - V

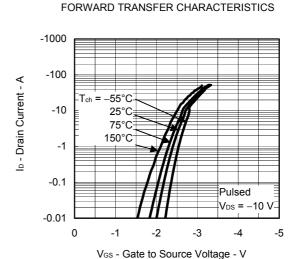
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

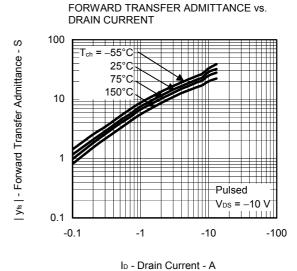


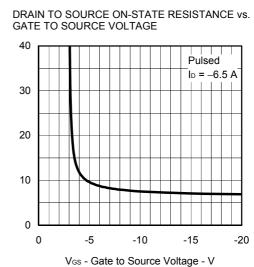




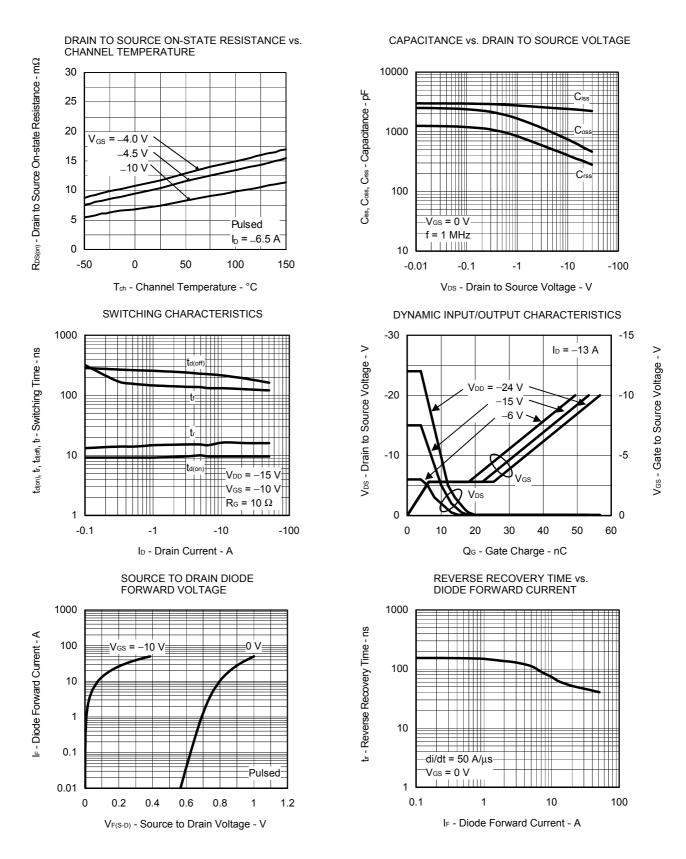






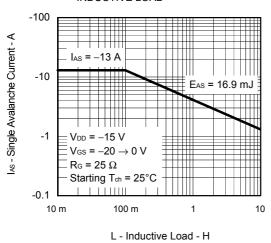


 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$ - Drain to Source On-state Resistance - m Ω

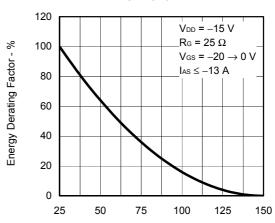


NEC μ PA2711GR

SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD



SINGLE AVALANCHE ENERGY DERATING FACTOR



Starting T_{ch} - Starting Channel Temperature - $^{\circ}$ C

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